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1

Electrical ratings

Parameter	Value	Unit
Drain-source voltage	40	
Gate-source voltage	± 20	V
Drain current (continuous) at $T_C = 25 \text{ °C}$	180	А
Drain current (continuous) at T _C = 100 °C	180	А
Drain current (pulsed)	720	А
Total dissipation at $T_C = 25 \text{ °C}$	300	W
Single pulse avalanche energy	1000	mJ
Storage temperature	- 55 to 175	°C
Operating junction temperature	- 55 10 175	°C
	Drain-source voltageGate-source voltageDrain current (continuous) at $T_C = 25$ °CDrain current (continuous) at $T_C = 100$ °CDrain current (pulsed)Total dissipation at $T_C = 25$ °CSingle pulse avalanche energyStorage temperature	Drain-source voltage40Gate-source voltage ± 20 Drain current (continuous) at $T_C = 25 \ ^{\circ}C$ 180Drain current (continuous) at $T_C = 100 \ ^{\circ}C$ 180Drain current (pulsed)720Total dissipation at $T_C = 25 \ ^{\circ}C$ 300Single pulse avalanche energy1000Storage temperature $-55 \ to 175$

Table 2. Absolute maximum ratings

1. Current limited by package.

2. Pulse width limited by safe operating area

3. Starting T_J=25°C, I_D=80 A, V_{DD}=32 V

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	0.5	°C/W
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb max	35	°C/W

1. When mounted on FR-4 board of 1 inch², 2oz Cu.



2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0, I _D = 250 μA	40			V
. Zero gate voltage		$V_{GS} = 0, V_{DS} = 40 V$			10	μΑ
I _{DSS} drain current	V _{GS} = 0, V _{DS} = 40 V, T _C =125 °C			100	μA	
I _{GSS}	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 20 V$			±200	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2		4	V
R _{DS(on)}	Static drain-source on- resistance	V _{GS} = 10 V, I _D = 80 A		1.4	1.7	mΩ

Table 4. On /off states

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance		-	7400	-	pF
C _{oss}	Output capacitance	V _{DS} = 25 V, f = 1 MHz,	-	1800	-	pF
C _{rss}	Reverse transfer capacitance	$V_{GS} = 0$	-	50	-	pF
Qg	Total gate charge	V _{DD} = 20 V, I _D = 160 A,	-	110	150	nC
Q _{gs}	Gate-source charge	V _{GS} = 10 V	-	30	-	nC
Q _{gd}	Gate-drain charge	(see Figure 14)	-	25	-	nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time		-	25	-	ns
t _r	Rise time	V _{DD} = 20 V, I _D = 80 A, R _G = 4.7 Ω, V _{GS} = 10 V	-	180	-	ns
t _{d(off)}	Turn-off delay time	(see <i>Figure 2</i>)	-	110	-	ns
t _f	Fall time		-	45	-	ns



Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		180	Α
I _{SDM} ⁽²⁾	Source-drain current (pulsed)		-		720	Α
V_{SD} $^{(3)}$	Forward on voltage	I _{SD} = 180 A, V _{GS} = 0	-		1.5	V
t _{rr}	Reverse recovery time	I _{SD} = 160 A, di/dt = 100 A/µs	-	70		ns
Q _{rr}	Reverse recovery charge	V _{DD} = 32 V, T _J =150 °C	-	225		nC
I _{RRM}	Reverse recovery current	(see Figure 15)	-	3.2		Α

Table 7. Source drain diode

1. Current limited by package

2. Pulse width limited by safe operating area.

3. Pulsed: pulse duration=300 µs, duty cycle 1.5%



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t_P(s)

Electrical characteristics (curves) 2.1

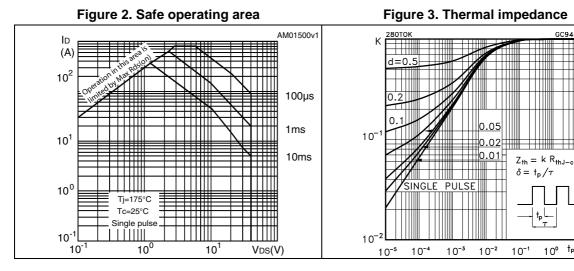


Figure 4. Output characteristics

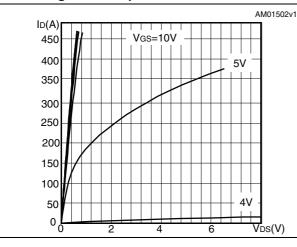


Figure 6. Gate charge vs gate-source voltage

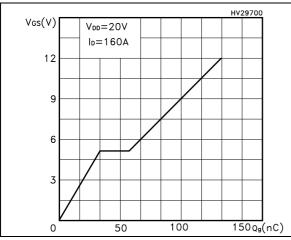


Figure 5. Transfer characteristics

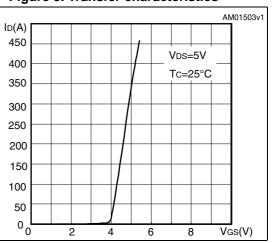
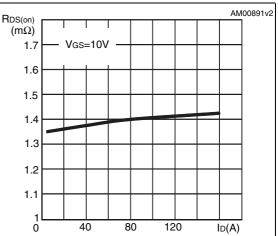


Figure 7. Static drain-source on-resistance





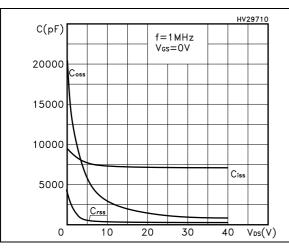


Figure 8. Capacitance variations

Figure 10. Normalized on-resistance vs temperature

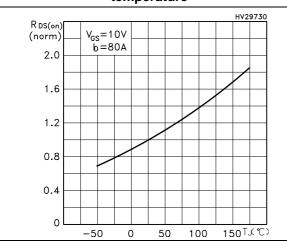
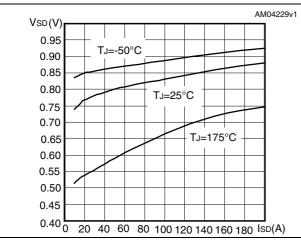


Figure 12. Drain-source diode forward characteristics



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Figure 9. Normalized gate threshold voltage vs temperature

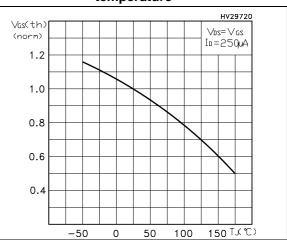
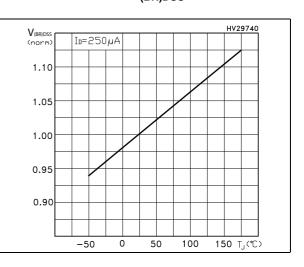
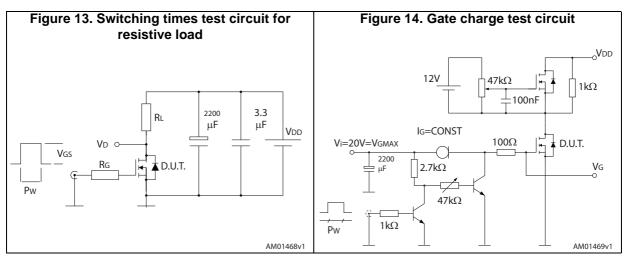
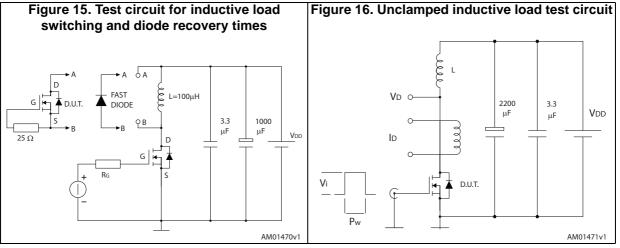


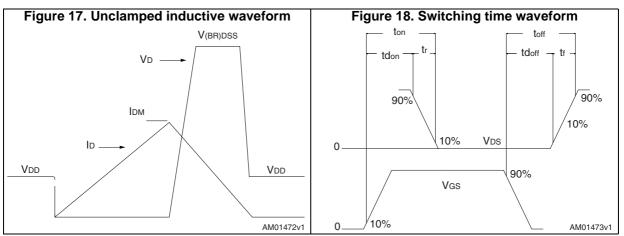
Figure 11. Normalized $\rm V_{(BR)DSS}$ vs temperature



3 Test circuits





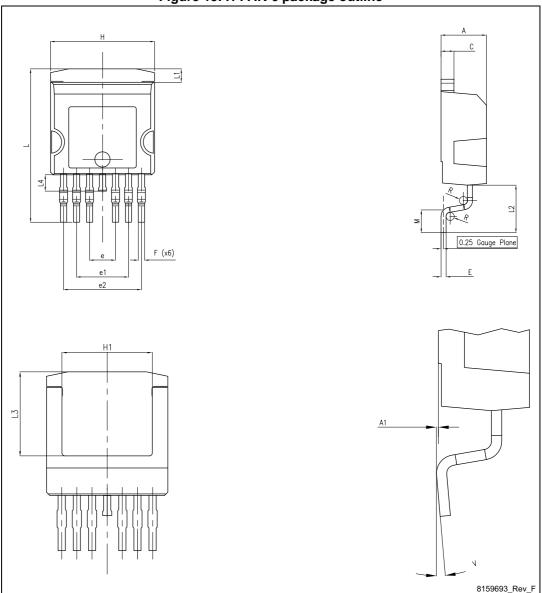


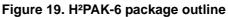


4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

4.1 H²PAK-6 package information







Dim	mm					
Dim.	Min.	Тур.	Max.			
А	4.30		4.80			
A1	0.03		0.20			
С	1.17		1.37			
е	2.34		2.74			
e1	4.88		5.28			
e2	7.42		7.82			
E	0.45		0.60			
F	0.50		0.70			
Н	10.00		10.40			
H1	7.40	-	7.80			
L	14.75		15.25			
L1	1.27		1.40			
L2	4.35		4.95			
L3	6.85		7.25			
L4	1.5		1.75			
М	1.90		2.50			
R	0.20		0.60			
V	0°		8°			

Table 8. H²PAK-6 package mechanical data

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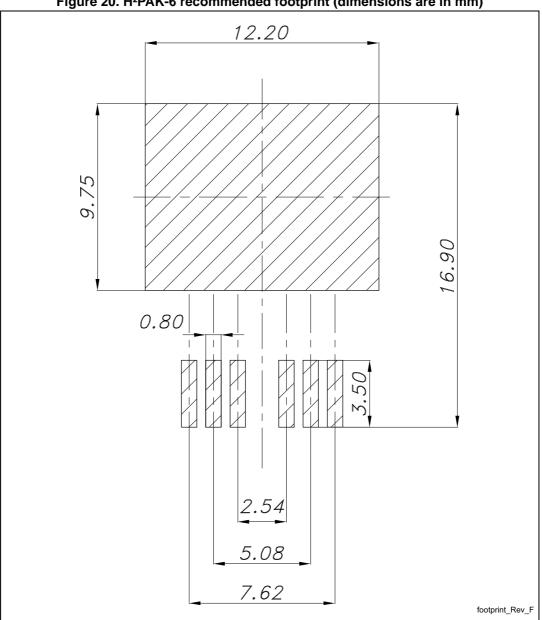


Figure 20. H²PAK-6 recommended footprint (dimensions are in mm)



5 Packing information

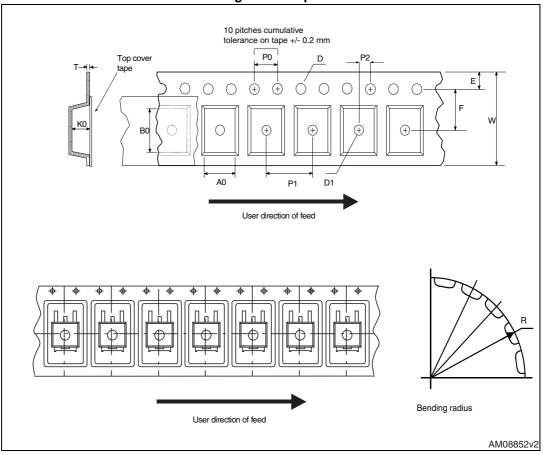


Figure 21. Tape



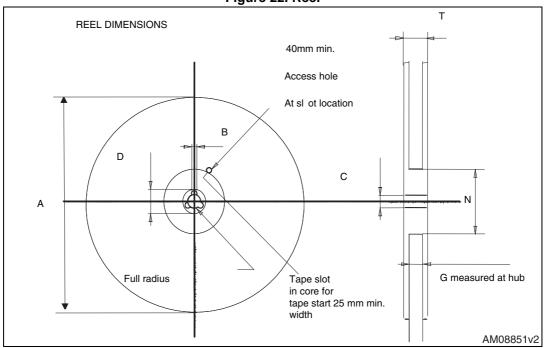


Figure 22. Reel

	Таре			Reel		
Dim.	m	m	Dim.	mm		
Dim.	Min.	Max.	Dim.	Min.	Max.	
A0	10.5	10.7	А		330	
B0	15.7	15.9	В	1.5		
D	1.5	1.6	С	12.8	13.2	
D1	1.59	1.61	D	20.2		
E	1.65	1.85	G	24.4	26.4	
F	11.4	11.6	Ν	100		
K0	4.8	5.0	Т		30.4	
P0	3.9	4.1				
P1	11.9	12.1		Base qty	1000	
P2	1.9	2.1		Bulk qty	1000	
R	50					
Т	0.25	0.35				
W	23.7	24.3				



6 Revision history

Table 10.	Document	revision	history
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Date	Revision	Changes
22-May-2015	1	First release. Part number previously included in datasheet DocID16957.



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